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Autorney's Docket No. 5308-157IP2

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Le e: Das et al.

Confirmation No.: 3570

Serial No.: 10/045,542

Group Art Unit: 1762

Filed: For:

Filed: October 26, 2001

METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON CARBIDE

LAYER UTILIZING AN ANNEAL IN A HYDROGEN ENVIRONMENT

Date: August 27, 2002

Commissioner for Patents Washington, DC 20231

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

Attached is a form PTO-1449, together with a copy of the identified document(s). This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Accordingly, no fee is required.

The Commissioner is hereby authorized to charge any additional fee that may be required or credit any refund to our Deposit Account No. 50-0220.

Respectfully submitted,

Timothy-J. O'Sullivan Registration No. 35,632

Customer Number:

20792

PATENT TRADEMARK OFFICE

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231 on August 27, 2002.

Traci A. Brown

Date of Signature: August 27, 2002

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